

## DESCRIPTION

The SSF2341E uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as -2.5V.

## GENERAL FEATURES

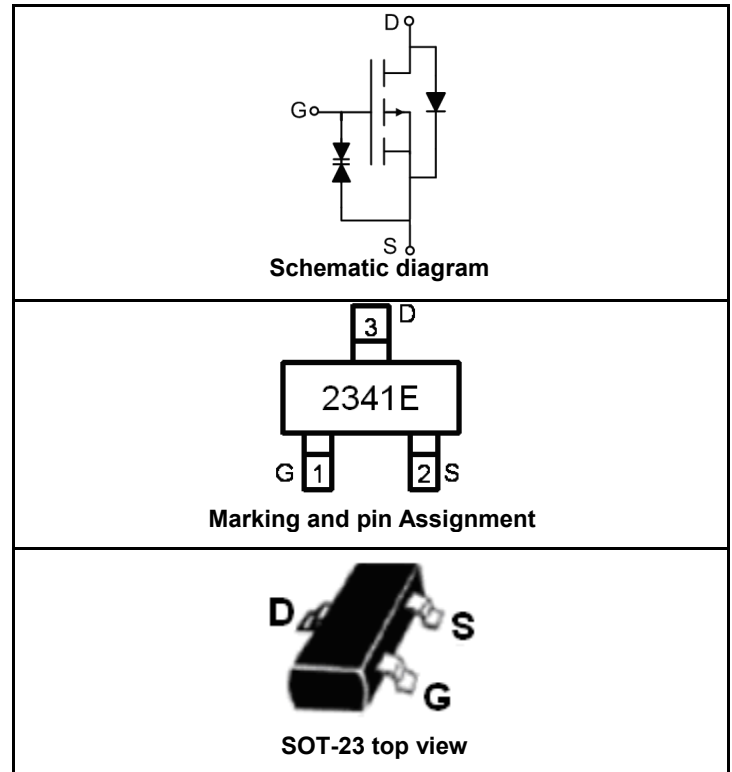
- $V_{DS} = -20V, I_D = -4A$   
 $R_{DS(ON)} < 73m\Omega @ V_{GS} = -1.8V$   
 $R_{DS(ON)} < 54m\Omega @ V_{GS} = -2.5V$   
 $R_{DS(ON)} < 43m\Omega @ V_{GS} = -4.5V$

ESD Rating: 3000V HBM

- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package

## Application

- Battery protection
- Load switch
- Power management



## PACKAGE MARKING AND ORDERING INFORMATION

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
2341E	SSF2341E	SOT-23	Ø330mm	12mm	3000 units

## ABSOLUTE MAXIMUM RATINGS(TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	-20	V
Gate-Source Voltage	$V_{GS}$	±8	V
Drain Current-Continuous@ Current-Pulsed (Note 1)	$I_D$	-4	A
	$I_{DM}$	-30	A
Maximum Power Dissipation	$P_D$	1.4	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	°C

## THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	90	°C/W
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## ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-20			V

Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-16V, V_{GS}=0V$			-1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 8V, V_{DS}=0V$			$\pm 10$	$\mu A$
<b>ON CHARACTERISTICS (Note 3)</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.3	-0.55	-1	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=-4.5V, I_D=-4A$		37	43	$m\Omega$
		$V_{GS}=-2.5V, I_D=-4A$		45	54	$m\Omega$
		$V_{GS}=-1.8V, I_D=-2A$		56	73	$m\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=-5V, I_D=-4A$	4	8		S
<b>DYNAMIC CHARACTERISTICS (Note4)</b>						
Input Capacitance	$C_{iss}$	$V_{DS}=-10V, V_{GS}=0V, F=1.0MHz$		1450		PF
Output Capacitance	$C_{oss}$			200		PF
Reverse Transfer Capacitance	$C_{rss}$			160		PF
<b>SWITCHING CHARACTERISTICS (Note 4)</b>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-10V, I_D=-1A, V_{GS}=-4.5V, R_{GEN}=3\Omega$		9.5		nS
Turn-on Rise Time	$t_r$			17		nS
Turn-Off Delay Time	$t_{d(off)}$			90		nS
Turn-Off Fall Time	$t_f$			30		nS
Total Gate Charge	$Q_g$	$V_{DS}=-10V, I_D=-4A, V_{GS}=-4.5V$		17		nC
Gate-Source Charge	$Q_{gs}$			1.3		nC
Gate-Drain Charge	$Q_{gd}$			4.5		nC
<b>DRAIN-SOURCE DIODE CHARACTERISTICS</b>						
Diode Forward Voltage (Note 3)	$V_{SD}$	$V_{GS}=0V, I_S=-1A$		-0.76	-1	V

## NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on 1in<sup>2</sup> FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production testing.

## TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

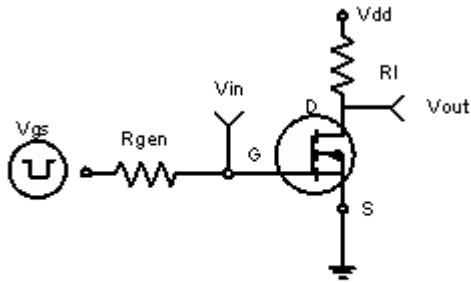


Figure 1: Switching Test Circuit

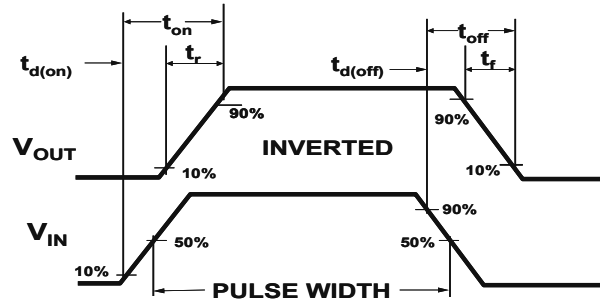


Figure 2: Switching Waveforms

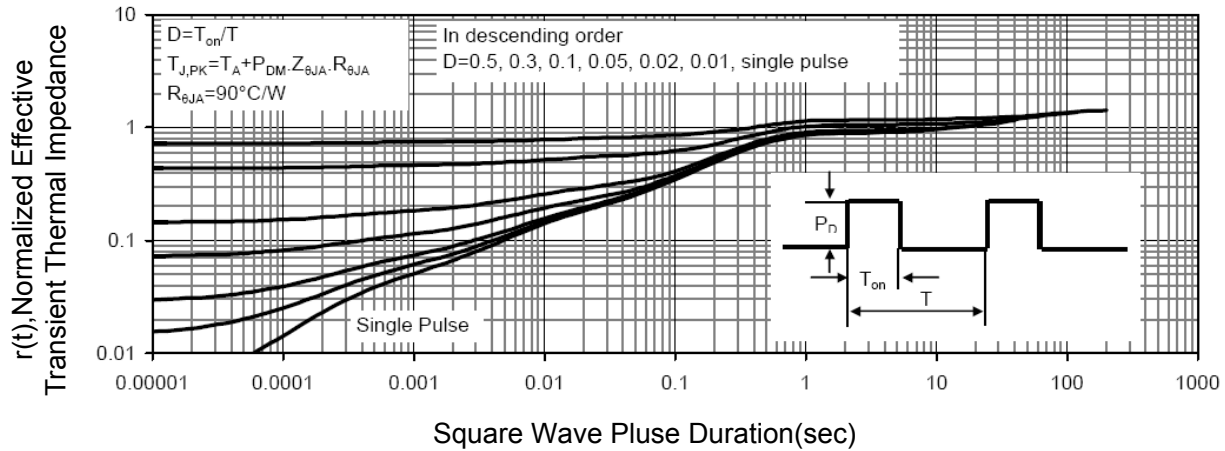
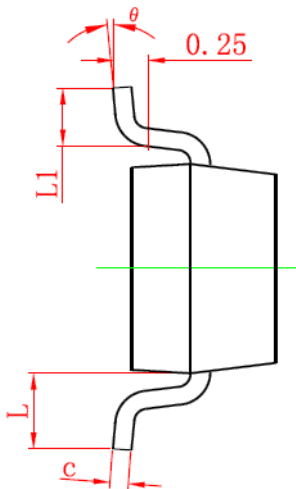
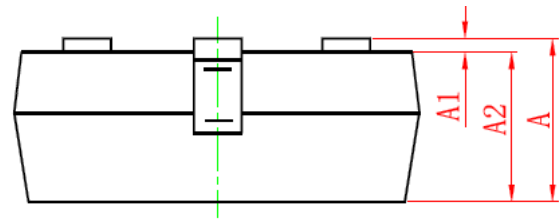
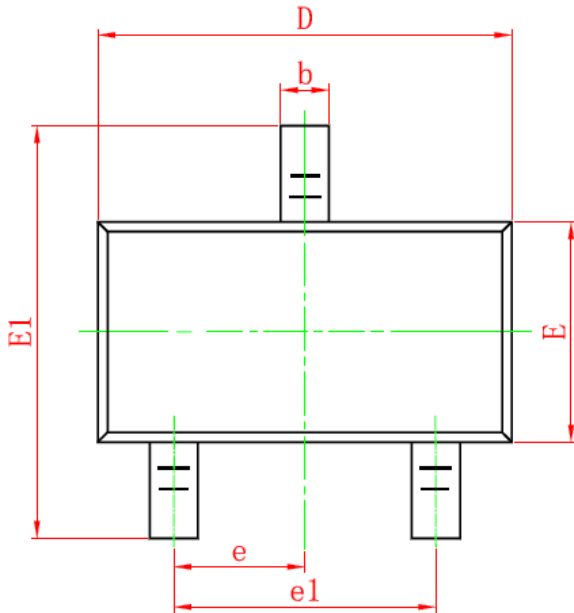


Figure 3 Normalized Maximum Transient Thermal Impedance

## SOT-23 PACKAGE INFORMATION

Dimensions in Millimeters (UNIT:mm)



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
$\theta$	0°	8°

### NOTES

1. All dimensions are in millimeters.
2. Tolerance  $\pm 0.10\text{mm}$  (4 mil) unless otherwise specified
3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
4. Dimension L is measured in gauge plane.
5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.

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